

Description

The HSP80N20 is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

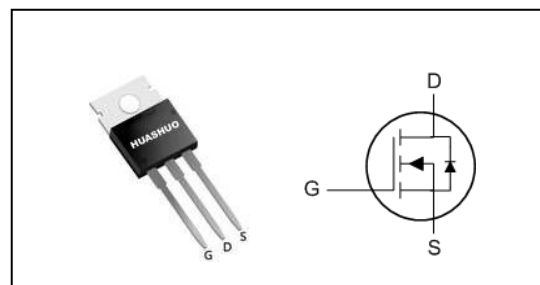
The HSP80N20 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- Power Switching application
- Green Device Available
- Excellent $C_{dv/dt}$ effect decline
- Advanced high cell density Trench technology

Product Summary

V_{DS}	200	V
$R_{DS(ON),typ}$	20	m Ω
I_D	80	A

TO220 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	200	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, V_{GS} @ 10V ¹	80	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, V_{GS} @ 10V ¹	55	A
I_{DM}	Pulsed Drain Current ²	280	A
EAS	Single Pulse Avalanche Energy ³	400	mJ
$P_D@T_C=25^\circ C$	Total Power Dissipation ³	370	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	0.45	$^\circ C/W$



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	200	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =30A	---	20	24	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	2	3.3	4	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =200V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =200V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.1	---	Ω
Q _g	Total Gate Charge (10V)	V _{DS} =100V, V _{GS} =10V, I _D =30A	---	115	---	nC
Q _{gs}	Gate-Source Charge		---	32	---	
Q _{gd}	Gate-Drain Charge		---	20.3	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =100V, V _{GS} =10V, R _G =2.5Ω I _D =30A	---	27	---	ns
T _r	Rise Time		---	38	---	
T _{d(off)}	Turn-Off Delay Time		---	22	---	
T _f	Fall Time		---	23	---	
C _{iss}	Input Capacitance	V _{DS} =50V, V _{GS} =0V, f=1MHz	---	7490	---	pF
C _{oss}	Output Capacitance		---	267	---	
C _{riss}	Reverse Transfer Capacitance		---	37	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	80	A
I _{SM}	Pulsed Source Current ^{2,5}		---	---	280	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =30A, T _J =25°C	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=10V, L=0.5mH
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.



Typical Characteristics

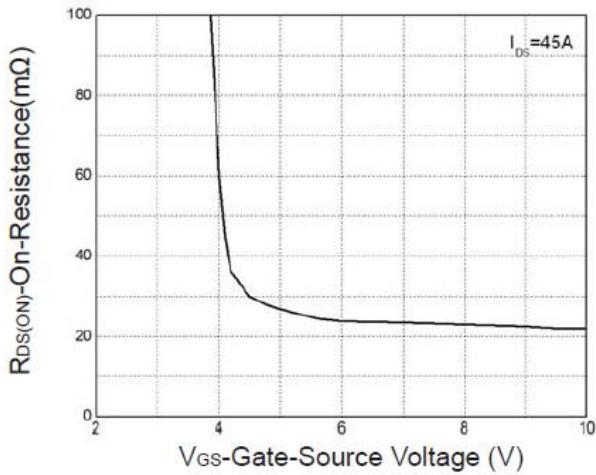


Fig.1 Gate-Source Vs.On-Resistance

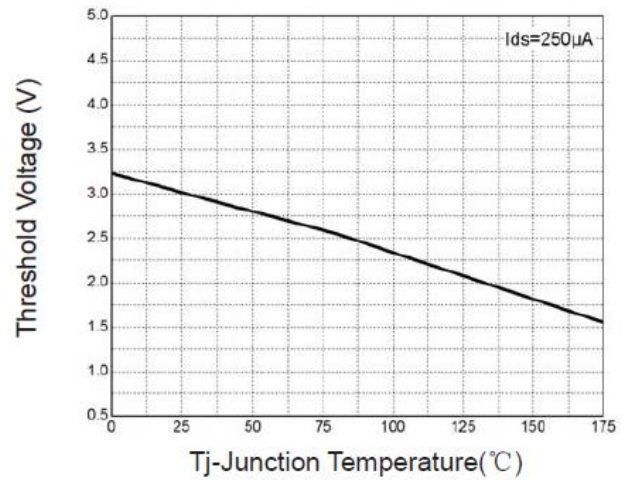


Fig.2 Gate-Source Forward

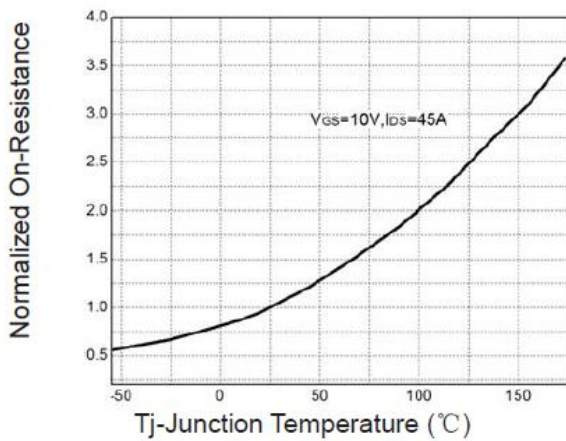


Fig.3 On-Resistance VS.Temperature

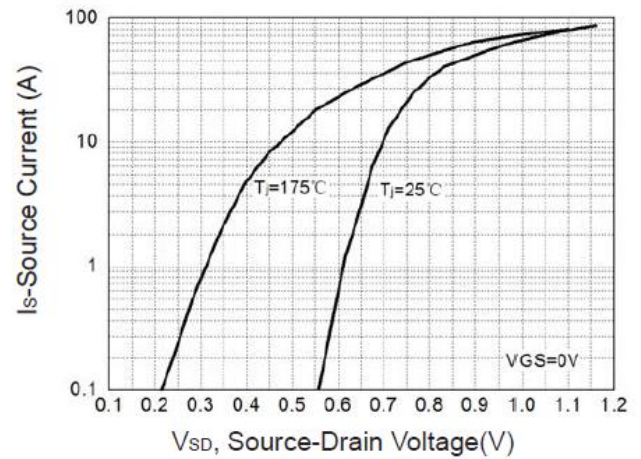


Fig.4 Source-Drain Diode Forward

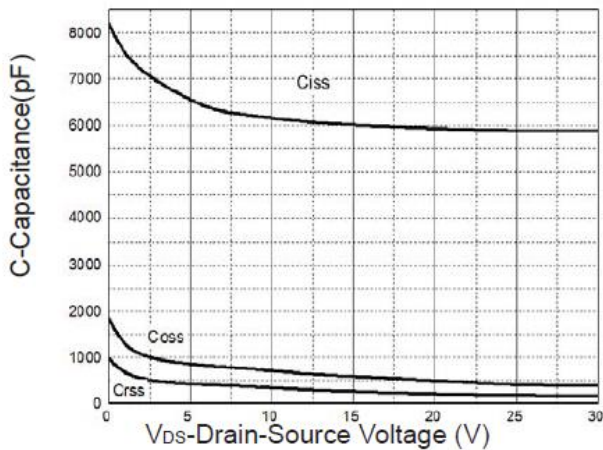


Fig.5 Capacitance Characteristics

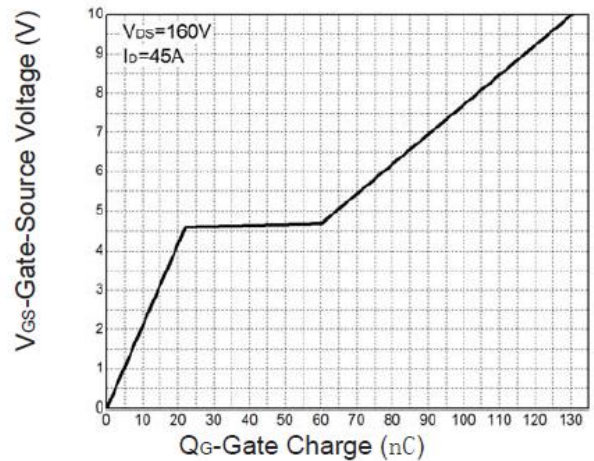


Fig.6 Gate Charge Characteristics



N-Ch 200V Fast Switching MOSFETs

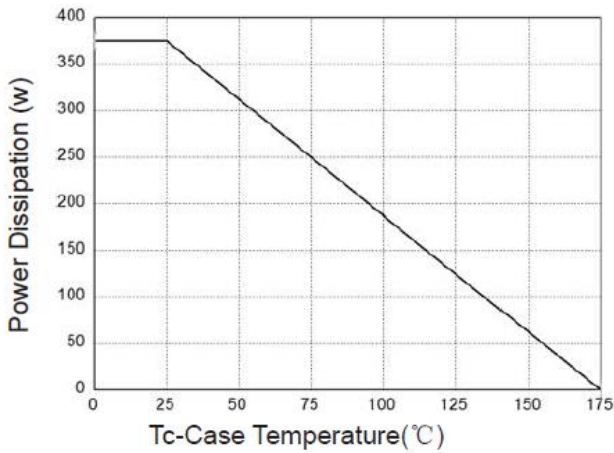


Fig.7 Power Dissipation

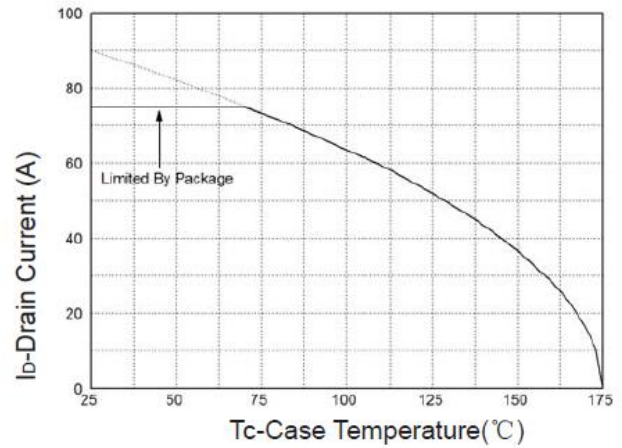


Fig.8 Drain Current

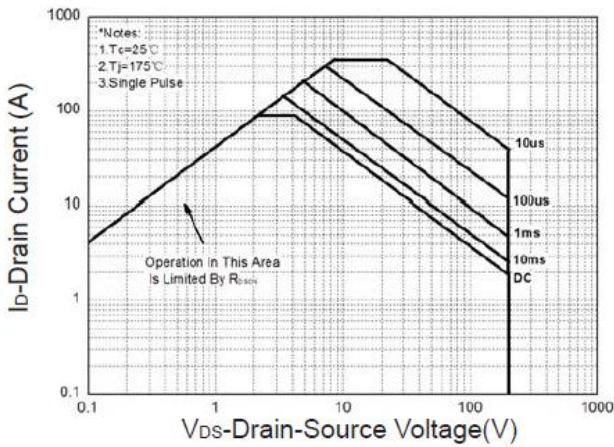
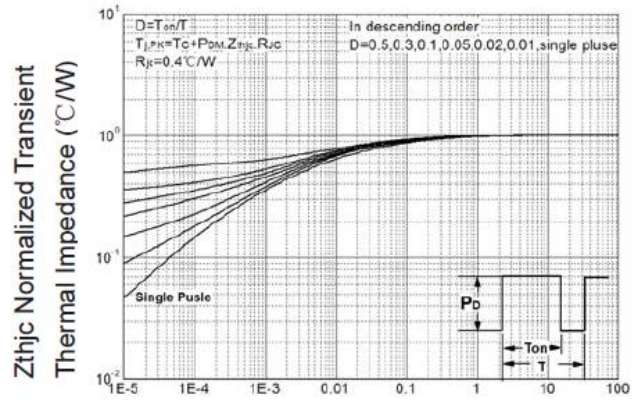


Fig.9 Safe Operation Area



Maximum Effective Transient Thermal Impedance, Junction-to-Case

Fig.10 Thermal Transient Impedance

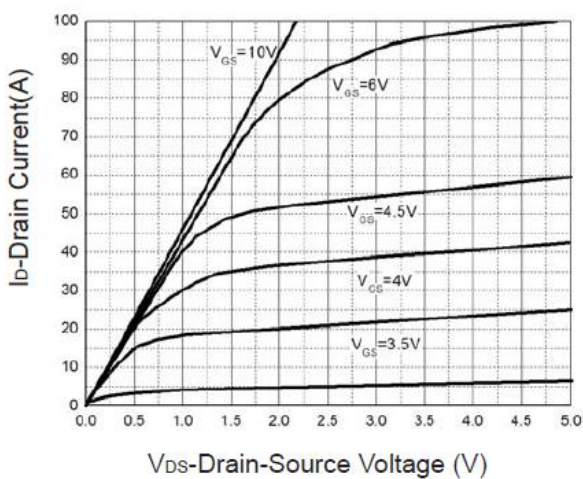


Fig.11 Output Characteristics

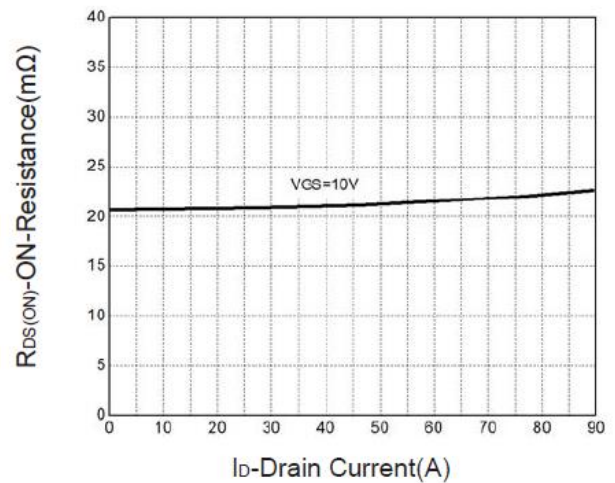
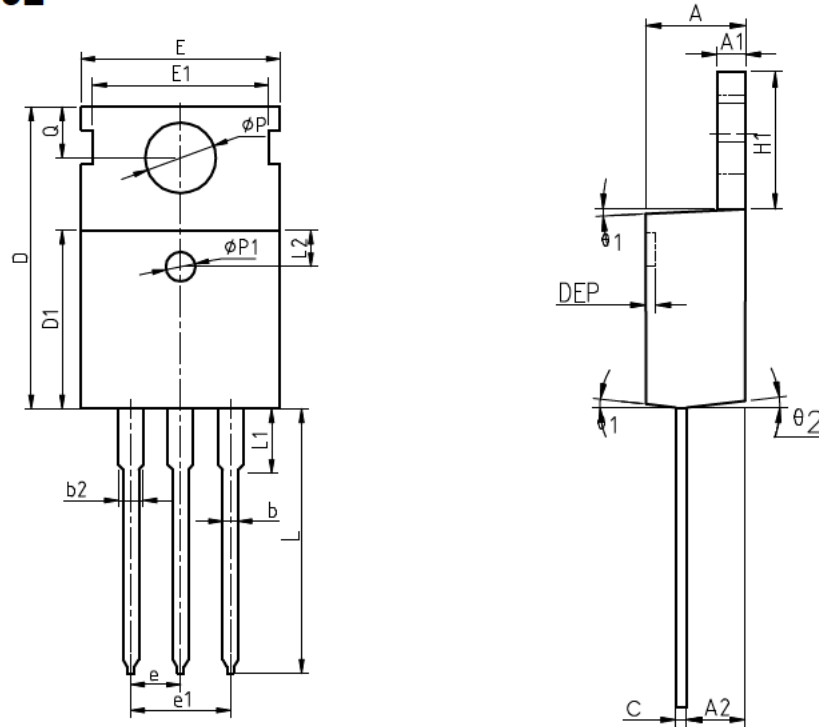


Fig.12 Drain-Source On Resistance



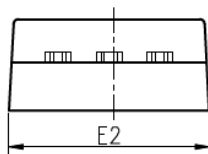
Package Information

TO-220FB-3L



COMMON DIMENSIONS

SYMBOL	MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185
A1	1.27	1.30	1.33	0.050	0.051	0.052
A2	2.35	2.40	2.50	0.093	0.094	0.098
b	0.77	0.80	0.90	0.030	0.031	0.035
b2	1.17	1.27	1.36	0.046	0.050	0.054
c	0.48	0.50	0.56	0.019	0.020	0.022
D	15.40	15.60	15.80	0.606	0.614	0.622
D1	9.00	9.10	9.20	0.354	0.358	0.362
DEP	0.05	0.10	0.20	0.002	0.004	0.008
E	9.80	10.00	10.20	0.386	0.394	0.402
E1	-	8.70	-	-	0.343	-
E2	9.80	10.00	10.20	0.386	0.394	0.402
e		2.54	BSC		0.100	BSC
e1		5.08	BSC		0.200	BSC
H1	6.40	6.50	6.60	0.252	0.256	0.260
L	12.75	13.50	13.65	0.502	0.531	0.537
L1	-	3.10	3.30	-	0.122	0.130
L2		2.50	REF		0.098	REF
P	3.50	3.60	3.63	0.138	0.142	0.143
P1	3.50	3.60	3.63	0.138	0.142	0.143
Q	2.73	2.80	2.87	0.107	0.110	0.113
theta 1	5°	7°	9°	5°	7°	9°
theta 2	1°	3°	5°	1°	3°	5°
theta 3	1°	3°	5°	1°	3°	5°



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